

**Claims after this response:**

1. (Previously amended) A method for etching a III-V based compound comprising:  
creating a mask on said III-V based compound:  
placing said III-V based compound and said mask into a reactor having a pressure between about 2 mTorr to about 20 mTorr;  
introducing a first gas chosen from HBr, HI, and IBr into said reactor;  
introducing second gas of BCl<sub>3</sub> into said reactor; and  
exposing said III-V based compound to a gas plasma comprising said first and said second gas to etch smooth high aspect ratio sidewalls, wherein BCl<sub>3</sub> is present in said reactor at a concentration of about 5 percent to about 75 percent by volume.
2. (original) The method of Claim 1 wherein said III-V based compound comprises indium.
- 3.(original) The method of Claim 1 wherein said gas plasma is generated using a reactive ion etching system.
- 4.(original) The method of Claim 1 wherein said gas plasma is generated using a combined reactive ion etching and inductively coupled plasma system.
- 5.(original) The method of Claim 4 wherein a first radio frequency generator is operated in the range from about 0 to 200 watts and a second radio frequency generator is operated in the range from about 50-800 watts.
- 6.(Canceled)
- 7.(Canceled)
- 8.(original) The method of Claim 1 further comprising introducing CH<sub>4</sub> and H<sub>2</sub> into said reactor.

9.(original) The method of Claim 8 wherein the ratio of said CH<sub>4</sub> to said H<sub>2</sub> is in the range from 5:100 to 70:30.

10.(original) The method of Claim 1 wherein said III-V based compound is heated to an initial temperature of about 60°C.

11.(previously amended) A method for etching a III-V based compound comprising:  
creating a mask on said III-V based compound;  
placing said III-V based compound and said mask into a reactor having a pressure between about 2 mTorr to about 20 mTorr;  
introducing a first gas chosen from HBr, HI and IBr into said reactor;  
introducing second gas of BCl<sub>3</sub> into said reactor;  
introducing a third gas of CH<sub>4</sub>;  
introducing a fourth gas of H<sub>2</sub>; and  
exposing said III-V based compound to a gas plasma comprising said first, second third and said fourth gas to etch smooth high aspect ratio sidewalls.

12.(original) The method of Claim 11 wherein said III-V based compound comprises indium.

13.(original) The method of claim 11 wherein said gas plasma is generated using a reactive ion etching system.

14.(original) The method of Claim 11 wherein said gas plasma is generated using a combined reactive ion etching and inductively coupled plasma system.

15.(original) The method of Claim 14 wherein a first radio frequency generator is operated in the range from about 0 to 200 watts and a second radio frequency generator is operated in the range from about 50-800 watts.

16.(original) The method of Claim 11 wherein the concentration of said first gas is in the range from about 10 percent to about 75 percent by volume.

17.(Canceled)

18.(Canceled)

19.(previously amended) A method for etching a III-V based compound comprising:  
creating a mask on said III-V based compound;  
placing said III-V based compound and said mask into a reactor having a pressure between about 2 mTorr to about 20 mTorr;  
introducing a first gas chosen from group VII gaseous species into said reactor;  
introducing second gas of  $\text{BCl}_3$  into said reactor; and  
exposing said III-V based compound to a gas plasma comprising said first and said second gas to etch smooth high aspect ratio sidewalls, wherein  $\text{BCl}_3$  is present in said reactor at a concentration of about 5 percent to about 75 percent by volume.

20.(Currently amended) A method for etching a III-V based compound comprising:  
creating a mask on said III-V based compound;  
placing said III-V based compound and said mask into a reactor having a pressure between about 2 mTorr to about 20 mTorr;  
introducing a first gas of  $\text{BCl}_3$  into said reactor;  
introducing a second gas of  $\text{CH}_4$ ;  
introducing a third gas of  $\text{H}_2$  such that the ratio of said third gas to said second gas is less than one; and  
exposing said III-V based compound to a gas plasma comprising said first, second and third gas to etch smooth high aspect ratio sidewalls, wherein the ratio of said second gas to said third gas is about 2:1.

21.(Canceled)

#### REMARKS

The Examiner rejected Claim 18 under 35 U.S.C. 112, second paragraph, because the limitations "said third gas" and "said fourth gas" have insufficient antecedent basis. The above amendments cancel Claim 18.